TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC7MH238FK

#### 3-to-8 Line Decoder

The TC7MH238FK is an advanced high speed CMOS 3-to-8 decoder fabricated with silicon gate  $\rm C^2MOS$  technology.

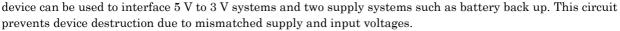
It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

When the device is enabled, 3 binary select inputs (A, B and C) determine which one of the outputs (Y0-Y7) will go high.

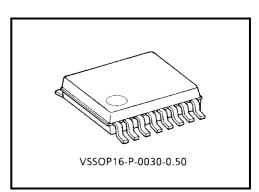
When enable input G1 is held low or either  $\overline{G}2A$  or  $\overline{G}2B$  is held high, decoding function is inhibited and all outputs go low.

G1,  $\overline{G}2A$  and  $\overline{G}2B$  inputs are provided to ease cascade connection and for use as an address decoder for memory systems.

An input protection circuit ensures that 0 to 7 V can be applied to the input pins without regard to the supply voltage. This



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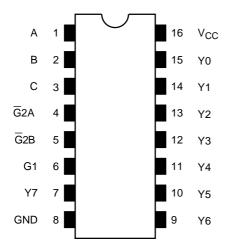


Weight: 0.02 g (typ.)

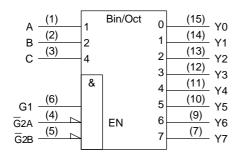
### **Features**

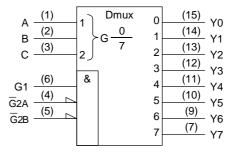
- High speed:  $t_{pd} = 5.5 \text{ ns (typ.)} (V_{CC} = 5 \text{ V})$
- Low power dissipation:  $I_{CC} = 4 \mu A \text{ (max) (Ta} = 25 ^{\circ}\text{C)}$
- High noise immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays:  $t_pLH \approx t_pHL$
- Wide operating voltage range:  $V_{CC (opr)} = 2 \sim 5.5 \text{ V}$
- Pin and function compatible with 74ALS238

# Pin Assignment (top view)



# **IEC Logic Symbol**





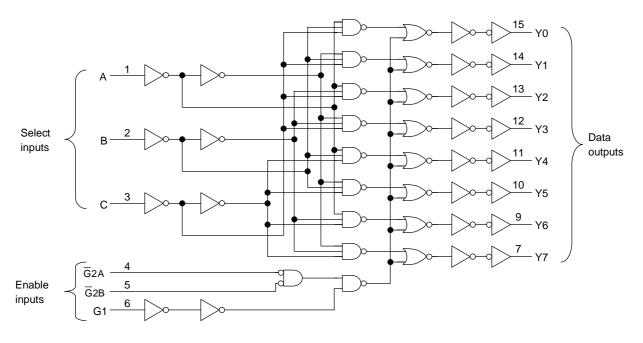
### **Truth Table**

Inputs					Outputs												
	Enable			Select		Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7	Selected Output			
G1	G <sub>2</sub> A	G <sub>2</sub> B	С	В	Α	10	Ť I	1 12	13	14	13	10	17				
L	Х	Х	Х	Х	Х	L	L	L	L	L	L	L	L	None			
Х	Н	Х	Х	Х	Х	L	L	L	L	L	L	L	L	None			
Х	Х	Н	Х	Х	Х	L	L	L	L	L	L	L	L	None			
Н	L	Ш	Ш	Ш	Ш	Н	<b>ا</b>	L	L	L	L	L	Ш	Y0			
Н	L	Ш	Ш	Ш	Ι	L	Ι	L	L	L	L	L	Ш	Y1			
Н	L	Ш	Ш	Ι	Ш	L	<b>ا</b>	Н	L	L	L	L	Ш	Y2			
Н	L	L	L	Н	Н	L	L	L	Н	L	L	L	L	Y3			
Н	L	L	Н	L	L	L	L	L	L	Н	L	L	L	Y4			
Н	L	L	Н	L	Н	Ĺ	L	Ĺ	Ĺ	L	Н	L	L	Y5			
Н	L	L	Н	Н	L	L	L	L	L	L	L	Н	L	Y6			
Н	L	L	Н	Н	Н	L	L	L	L	L	L	L	Н	Y7			

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X: Don't care

# **System Diagram**



# **Maximum Ratings**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5~7.0	V
DC input voltage	V <sub>IN</sub>	-0.5~7.0	V
DC output voltage	V <sub>OUT</sub>	-0.5~V <sub>CC</sub> + 0.5	V
Input diode current	I <sub>IK</sub>	-20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V <sub>CC</sub> /ground current	Icc	±75	mA
Power dissipation	P <sub>D</sub>	180	mW
Storage temperature	T <sub>stg</sub>	-65~150	°C

# **Recommended Operating Conditions**

Characteristics	Symbol	Rating	Unit	
Supply voltage	V <sub>CC</sub>	2.0~5.5	V	
Input voltage	V <sub>IN</sub>	0~5.5	V	
Output voltage	V <sub>OUT</sub>	0~V <sub>CC</sub>	V	
Operating temperature	T <sub>opr</sub>	-40~85	ပ္	
Input rise and fall time	dt/dv	$0 \sim 100 \; (V_{CC} = 3.3 \pm 0.3 \; V)$	ns/V	
Imput rise and rail time	αι/αν	$0 \sim 20 \ (V_{CC} = 5 \pm 0.5 \ V)$		

# **Electrical Characteristics**

# **DC Characteristics**

Characte	Symbol	Test Condition			-	Га = 25°0		Ta = -4	Unit		
Characte	Onaracteristics		rest Condition		V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Unit
			_		2.0	1.50	_	_	1.50	_	V
Input voltage	High level	V <sub>IH</sub>			3.0~5.5	V <sub>CC</sub> × 0.7	_	_	V <sub>CC</sub> × 0.7		
input voitage					2.0	_	_	0.50	_	0.50	
	Low level	$V_{IL}$		_	3.0~5.5	_		$\begin{array}{c} V_{CC} \\ \times \ 0.3 \end{array}$	_	$\begin{array}{c} V_{CC} \\ \times  0.3 \end{array}$	
	High level	Voн	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -50 μA	2.0	1.9	2.0	_	1.9	_	
					3.0	2.9	3.0	_	2.9	_	
					4.5	4.4	4.5	_	4.4	_	
				$I_{OH} = -4 \text{ mA}$	3.0	2.58			2.48		
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	3.80	1	V								
Output voltage	Low level	V <sub>OL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	Ι <sub>ΟL</sub> = 50 μΑ	2.0	_	0	0.1	_	0.1	- -
					3.0	_	0	0.1	_	0.1	
					4.5	_	0	0.1	_	0.1	
				$I_{OL} = 4 \text{ mA}$	3.0	_		0.36	_	0.44	
				$I_{OL} = 8 \text{ mA}$	4.5	_		0.36	—	0.44	
Input leakage current		I <sub>IN</sub>	V <sub>IN</sub> = 5.5 V or GND		0~5.5	_	_	±0.1	—	±1.0	μΑ
Quiescent supply current		Icc	V <sub>IN</sub> = V <sub>CC</sub> or GND		5.5	_	_	4.0	_	40.0	μΑ

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# AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Cumbal	Test Condition			Ta = 25°C			Ta = -4	Unit	
Characteristics	Symbol	rest Condition	V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	Min	Тур.	Max	Min	Max	Unit
	t <sub>pLH</sub>		3.3 ± 0.3	15	_	8.0	12.3	1.0	14.5	ns
Propagation delay time			3.5 ± 0.5	50		10.5	15.8	1.0	18.0	
(A, B, C-Y)	tpHL		5.0 ± 0.5	15		5.5	8.1	1.0	9.5	113
			5.0 ± 0.5	50		7.0	10.1	1.0	11.5	
	t <sub>pLH</sub>	_	3.3 ± 0.3	15		8.1	12.8	1.0	15.0	ns
Propagation delay time				50		10.6	16.3	1.0	18.5	
(G1-Y)	tpHL		5.0 ± 0.5	15	_	5.4	8.1	1.0	9.5	
			3.0 ± 0.3	50		6.9	10.1	1.0	Max 14.5 18.0 9.5 11.5 15.0 18.5	
	<sup>t</sup> pLH <sup>t</sup> pHL	_	3.3 ± 0.3	15		8.1	12.3	1.0	14.5	
Propagation delay time				50	_	10.6	15.8	1.0	18.0	
( <del>G</del> 2 -Y)			5.0 ± 0.5	15	_	5.7	8.1	1.0	9.5	
				50	_	7.2	10.1	1.0	11.5	
Input capacitance	C <sub>IN</sub>	-	_		_	4	_		10	pF
Power dissipation capacitance	C <sub>PD</sub>			(Note)	_	37	_	_		pF

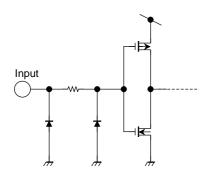
Note: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

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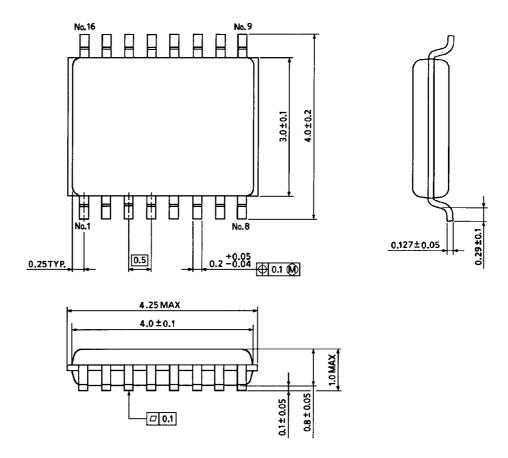
Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 

# **Input Equivalent Circuit**



# **Package Dimensions**



Weight: 0.02 g (typ.)

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